

SILICON NPN SWITCHING TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH CURRENT CAPABILITY

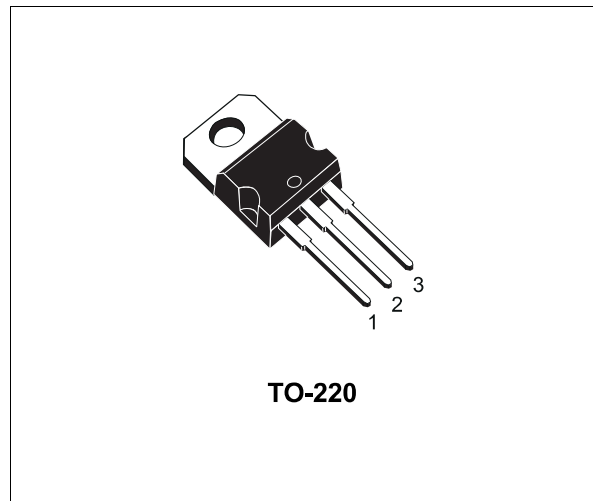
APPLICATIONS

- SWITCHING REGULATORS
- MOTOR CONTROL

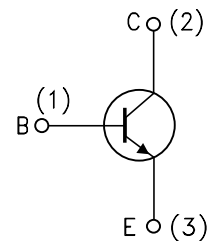
DESCRIPTION

The MJE13007A is silicon multiepitaxial mesa NPN power transistor mounted in Jedec TO-220 plastic package.

They are intended for use in motor control, switching regulators etc.



INTERNAL SCHEMATIC DIAGRAM



SC06960

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-Emitter Voltage ($V_{BE} = -1.5V$)	850	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	400	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	9	V
I_C	Collector Current	8	A
I_{CM}	Collector Peak Current	16	A
I_B	Base Current	4	A
I_{BM}	Base Peak Current	8	A
I_E	Emitter Current	12	A
I_{EM}	Emitter Peak Current	24	A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ C$	80	W
T_{stg}	Storage Temperature	-65 to 150	$^\circ C$
T_j	Max. Operating Junction Temperature	150	$^\circ C$